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JUNCTION VARACTOR WITH HIGH Q FACTOR

Appl. No. : 10/711,140 Confirmation No. 5139
Applicant : Ching-Hung Kao
Filed : August 27, 2004
TC/A.U. : 2818
Examiner : NGUYEN,
TRAM HOANG
Docket No. : NAUP0622USA0
Customer No. : 27765

Commissioner for Patents
P.O. Box 1450
Alexandria VA 22313-1450

AFFIDAVIT UNDER 37 CFR 1.132

5 I, Ching-Hung Kao, am the sole applicant in the instant application. I was one of two joint inventors in US Patent 6,882,029. In patent 6,882,029, I conceived of the idea that the LDD merges with the first ion diffusion region that serves an anode of the junction varactor. The other inventor in patent 6,882,029 did not conceive of this subject matter.

10 I am a Taiwan citizen and do not use a standard spelling of my name used for English-language documents. In the US Patent 6,882,029, my name was spelled as "Jing-Horng Gau", but in the instant application, my name was spelled as "Ching-Hung Kao". As evidenced by the attached declaration from US Patent 6,882,029 having attorney docket number NAUP0550USA, my address used in the instant application is the

same as my address used in the patent 6,882,029. Therefore, I state that I am the sole inventor of this claimed subject matter.

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(Ching-Hung Kao)Date: 2006/05/25

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